

DDR3 Power Solutions

TPS51116 – 3V-28Vin controller + 3A LDO for DDR I/II/III

ONE OF THE WORLD'S MOST POPULAR DDR POWER SOLUTIONS

Features

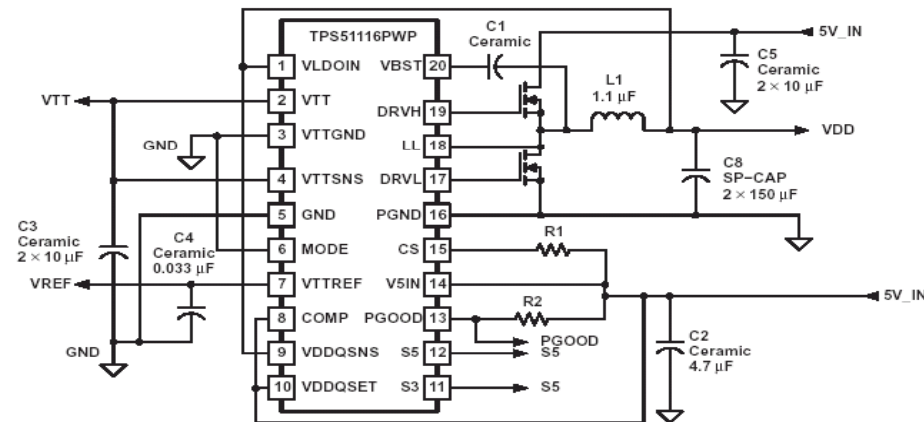
- Adaptive On-Time Current Mode control
- D-CAP™ Mode for Integrated Loop Compensation
- Selectable Current Mode Option
- Integrated sleep state control for S3/S4/S5 States
- Current Sensing from both R_{DSon} or Resistor
- Configurable for 2.5V (DDR), 1.8V (DDR II), 1.5V (DDR3), 1.35V (LPDDR3), or Adj.
- LDO Input Available
- Capable to Sink and Source 3A Peak
- Requires only **20uF Ceramic Output Capacitor**
- Buffered Low Noise 10mA VTTREF Output
- Accuracy +/-20mV for both VTT and VTTREF
- OVP, UVP, Thermal Shutdown, Power Good

Benefits

- Fastest Transient Response, lowest output ripple
- No loop compensation makes easier to use
- Supports all output cap. types including ceramic
- Supports High-Z in S3 and Discharge in S4/S5
- High efficiency or high current sense accuracy
- Flexibility to support all DDR systems
- Reduces total power dissipation
- Can power high-current DDR termination
- Low BOM cost, small PCB area
- Meets JEDEC DDR Power requirements
- Meets JEDEC DDR Power requirements
- Full suite of system protection

Applications:

- DDR I / DDR II / DDR III Memory Termination
- SSTL-2, SSTL-3, HSTL Termination
- EVM available



Schedule of New DDR Power Products

Part Number	Application	Package	Eng. Sample Date	RTM Date
TPS51216/59216	DCAP/DCAP2 DDR3 or LPDDR3 controller with VTT LDO (1x 10uF) for 1.5V or other rail	20-pin 3x3 mm QFN 0.4mm pitch (RUK)	9/2010	Now
TPS51206	VTTLDO: 1A TDC/2A I _{max} /3A OCL	10-pin 2x2 mm SON 0.5mm pitch (DSQ)	10/2010	04/2011

TPS51216 - New DDR2/3/3L Solution

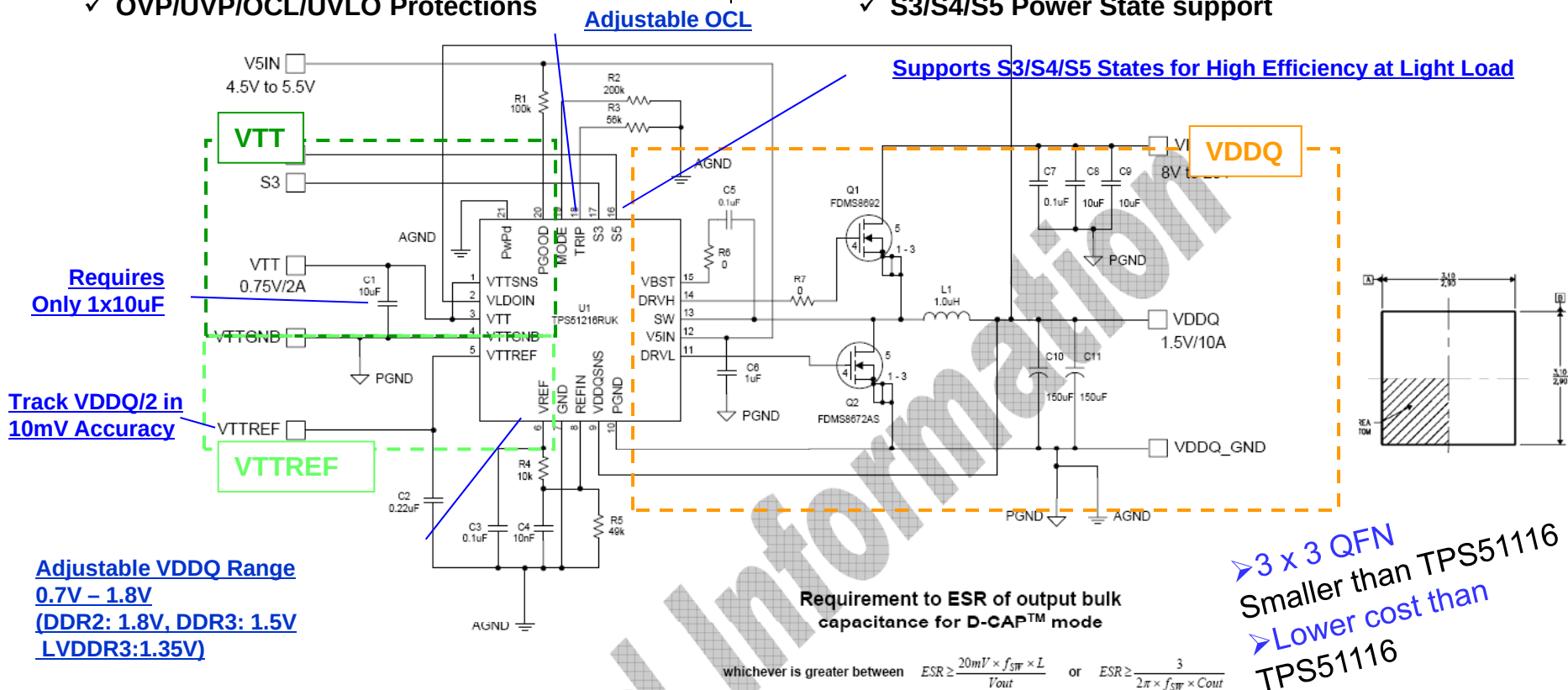
Features

- Synchronous Buck Controller (VDDQ)

- ✓ VIN:3V-28V, VDDQ:0.7V-1.8V
- ✓ 0.8% VREF Accuracy
- ✓ Selectable D-CAP™ 300kHz, 400kHz Fsw Architectures
- ✓ No External Compensation Required
- ✓ OVP/UVP/OCL/UVLO Protections

- ±2A LDO (VTT), Buffered Reference (VTTREF)

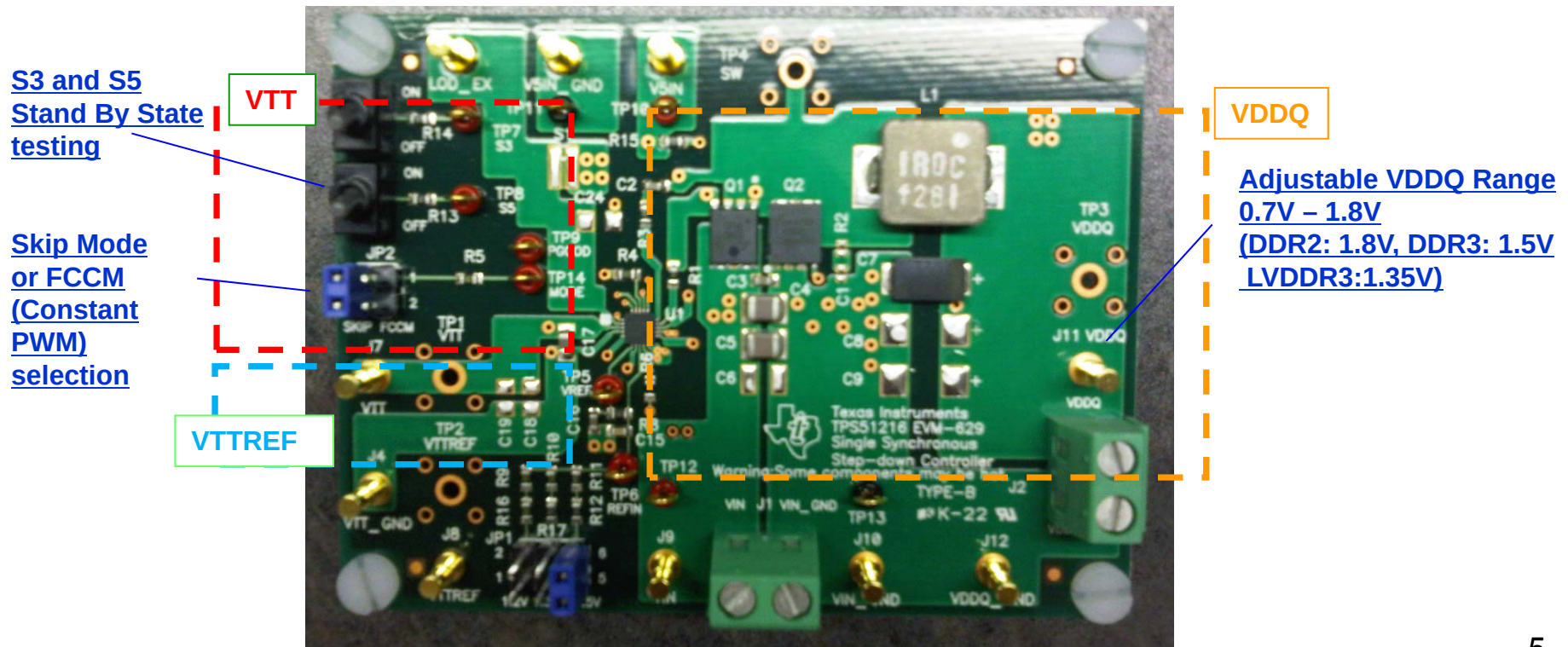
- ✓ 2A Peak Sink/Source Current (VTT)
- ✓ 10mA Buffered Low Noise Reference (VTTREF)
- ✓ LDO Input for Higher Efficiency
- ✓ 0.8% VTTREF, and 20mV VTT Accuracy
- ✓ Require Only 1x10uF Capacitor for VTT
- ✓ S3/S4/S5 Power State support



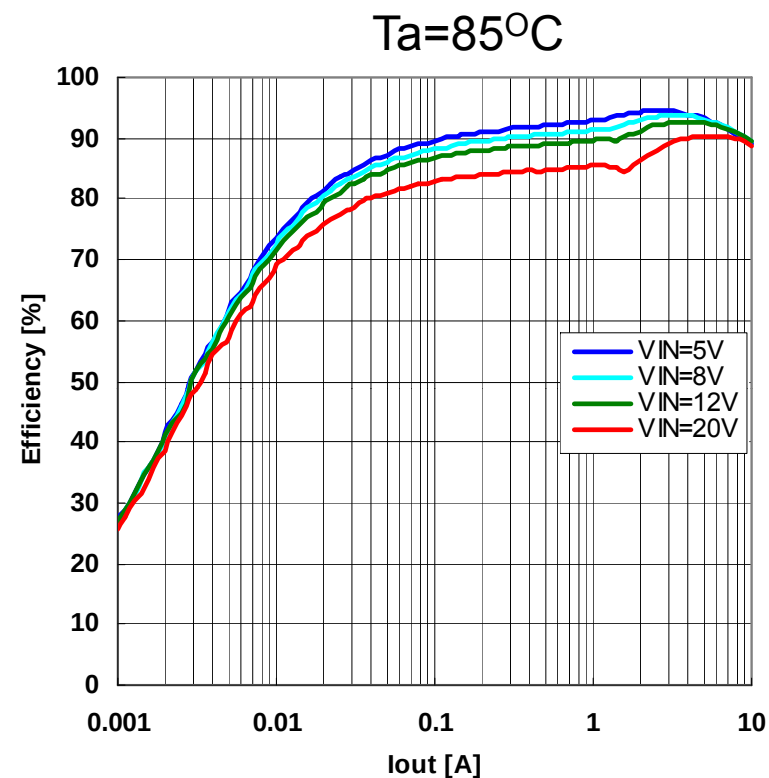
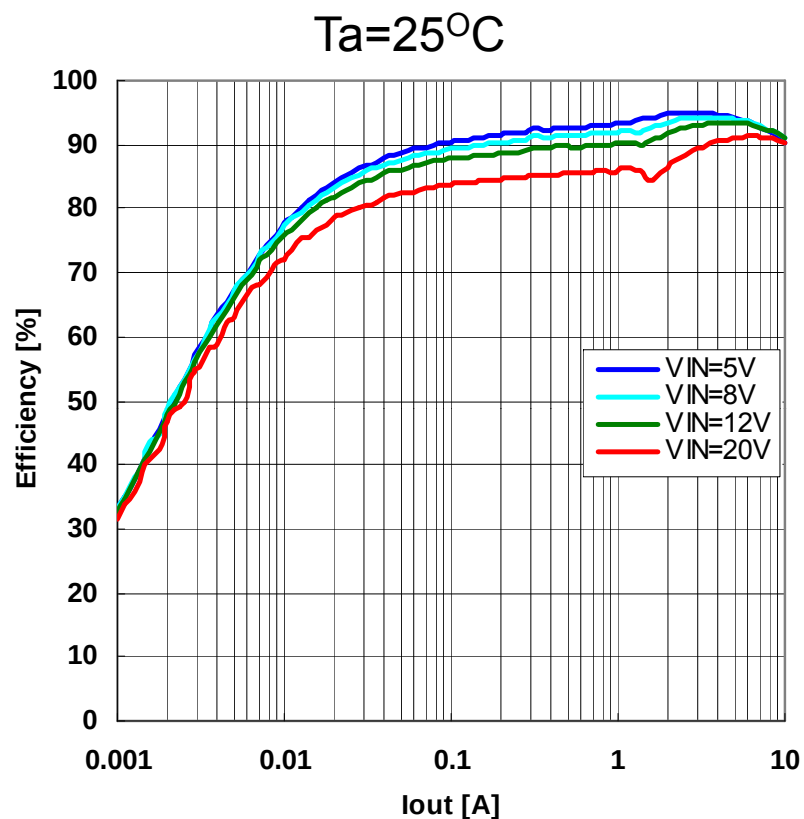
TPS51216 EVM - New DDR2/3/3L Solution

Features

- Complete DDR/DDR2/DDR3/LVDDR3 evaluation platform
- VIN, VOUT connections and all DDR-relevant test points

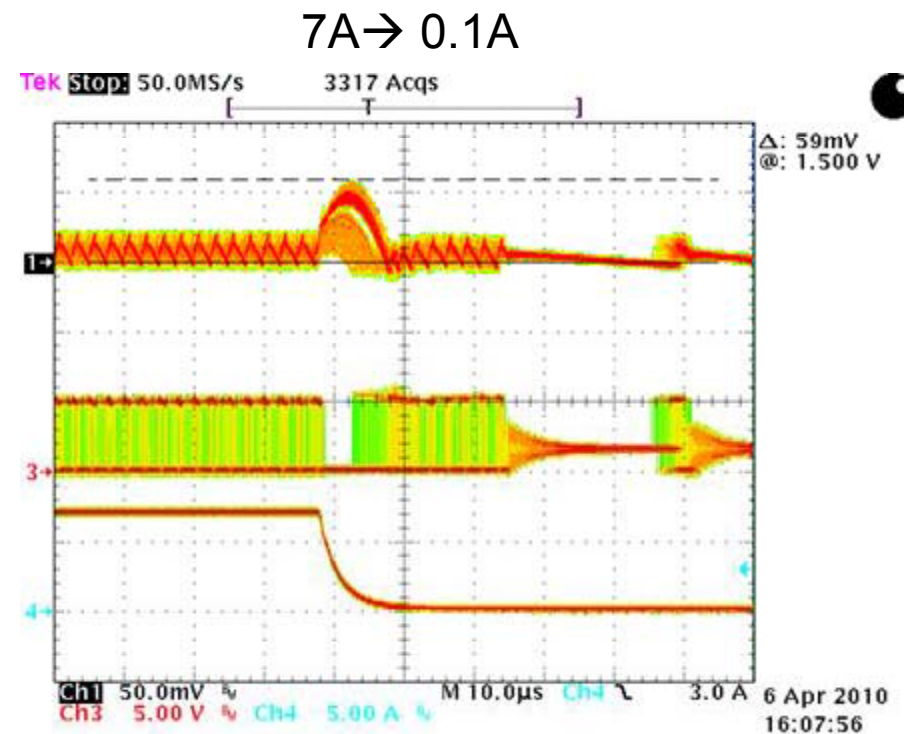
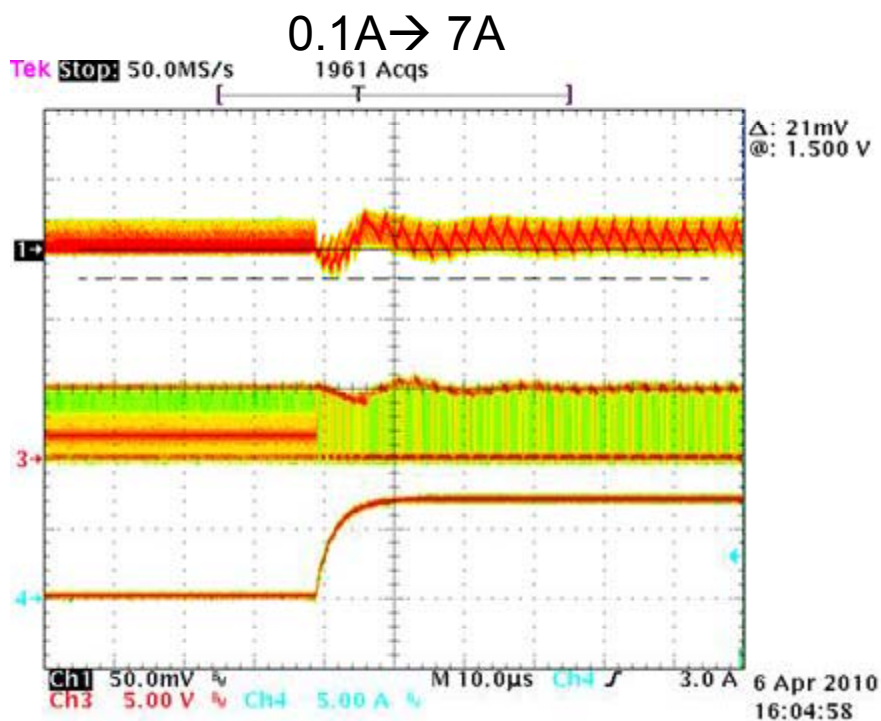


Efficiency Performance at 1.5V_{OUT}



Lx	1.0uH	1.0uH, 2.3mΩ, 18.5A	MPC1055L1R0C
C7	150uF	150uF, 15mΩ, 6.3V	EEFCX0J151R
C8	150uF	150uF, 15mΩ, 6.3V	EEFCX0J151R
Q1		30V, 28A, 9.0mΩ	FDMS8692
Q2		30V, 28A, 5.0mΩ	FDMS8672AS

Load Transient Performance



TPS51116 / TPS51216 Comparison

	TPS51116	TPS51216																										
Package	4x4mm- 24 pin, 0.5mm pitch	3x3 mm- 20pin, 0.4mm pitch																										
Switching Frequency	D-cap, 400kHz	D-cap: 300kHz/400kHz																										
VTTLDO	2 x 10uF decoupling	1 x 10uF decoupling																										
Voltage Feedback	Resistor divider of output voltage	Voltage reference divider; less jitter, voltage dynamic change support																										
Gate Drive	<table><tr><td rowspan="2">R_{DRVH}</td><td>DRVH resistance</td><td>Source, I_{DRVH} = 100 mA</td><td>3</td><td>6</td></tr><tr><td></td><td>Sink, I_{DRVH} = 100 mA</td><td>0.9</td><td>3</td></tr><tr><td rowspan="2">R_{DRVL}</td><td>DRVL resistance</td><td>Source, I_{DRVL} = 100 mA</td><td>3</td><td>6</td></tr><tr><td></td><td>Sink, I_{DRVL} = 100 mA</td><td>0.9</td><td>3</td></tr></table>	R _{DRVH}	DRVH resistance	Source, I _{DRVH} = 100 mA	3	6		Sink, I _{DRVH} = 100 mA	0.9	3	R _{DRVL}	DRVL resistance	Source, I _{DRVL} = 100 mA	3	6		Sink, I _{DRVL} = 100 mA	0.9	3	<table><tr><td>1.7</td><td>3.0</td></tr><tr><td>0.6</td><td>1.5</td></tr><tr><td>0.9</td><td>2.0</td></tr><tr><td>0.5</td><td>1.2</td></tr></table> Ω	1.7	3.0	0.6	1.5	0.9	2.0	0.5	1.2
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Zero Cross Detection	+/-6mV max comparator offset	Auto zero comparator																										

8

Smallest VTT LDO: TPS51206 (Sijimi)

Features

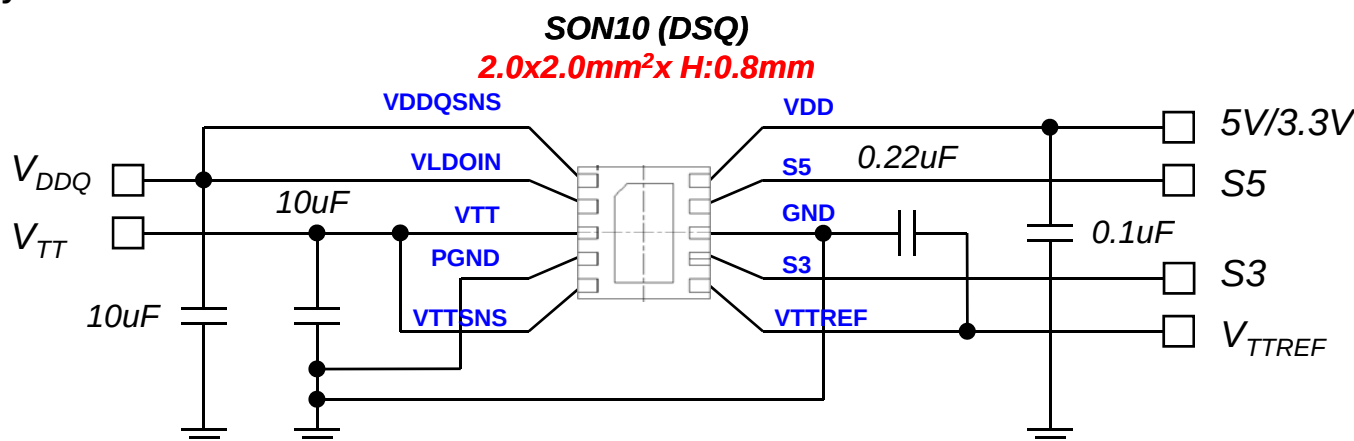
VTT / VTTREF

- 1A TDC, 2A peak sink/source VTT LDO
- 10mA buffered VTTREF LDO
- Supports high-Z in S3, soft-off discharge in S4/S5
- 1x10uF VTT output capacitance
- Supports 5V and 3.3V Vdd
- 2.0x2.0mm SON Package
- Pin Integrity with TPS51100

Benefits

VTT / VTTREF

- Compact solution size
- Support DDR2, DDR3, LPDDR3
- 50% reduction of VTT Cap footprint & cost
- Flexible for many platforms
- 73% reduction of IC footprint vs. TPS51100



STATE	S3	S5	VTTREF	VTT
S0	H	H	ON	ON
S3	L	H	ON	OFF (high-Z)
S4/S5	L	L	OFF (discharge)	OFF (discharge)

TPS51206 EVM - New DDR2/3/3L +/-2A VTT Solution

Features

- Complete DDR2/DDR3/LVDDR3 VTT (termination) evaluation platform
- VIN, VLDOIN, VDDQ IN, VOUT connections and all DDR VTT-relevant test points

